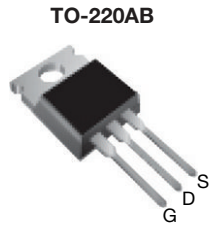


## E Series Power MOSFET



N-Channel MOSFET

### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Computing
  - PC silver box / ATX power supplies
- Lighting
  - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
  - Power factor correction (PFC)
  - Two switch forward converter
  - Flyback converter
- Switch mode power supplies (SMPS)

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	550	
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.243
$Q_g$ max. (nC)	66	
$Q_{gs}$ (nC)	8	
$Q_{gd}$ (nC)	14	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free and halogen-free	SiHP15N50E-BE3 <sup>a</sup>
	SiHP15N50E-GE3

#### Note

a. "-BE3" denotes alternate manufacturing location

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	500	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	28	
Linear Derating Factor		1.25	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	136	mJ
Maximum Power Dissipation	$P_D$	156	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C
Drain-Source Voltage Slope	$dV/dt$	70	V/ns
Reverse Diode $dV/dt$ <sup>d</sup>		27	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.1$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C



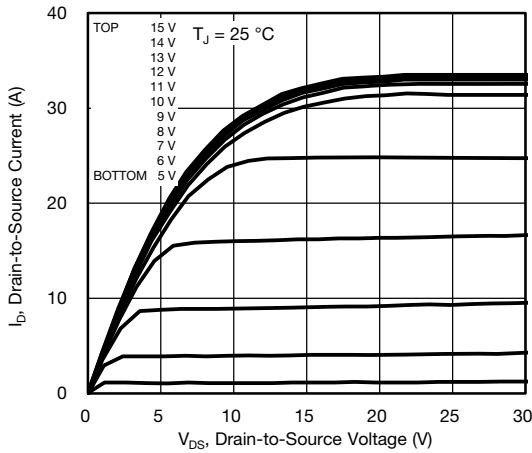
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.8	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT		
<b>Static</b>									
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V		
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.62	-	V/°C		
Gate-source threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V		
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA		
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$		
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	10	$\mu\text{A}$		
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	25			
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 7.5\text{ A}$	-	0.243	0.280	$\Omega$		
Forward transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 7.5\text{ A}$		-	3.9	-	S		
<b>Dynamic</b>									
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	1162	-	pF		
Output capacitance	$C_{oss}$			-	51	-			
Reverse transfer capacitance	$C_{rss}$			-	7	-			
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$			$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		-		55	-
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$					-		164	-
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 7.5\text{ A}, V_{DS} = 400\text{ V}$	-	33	66	nC		
Gate-source charge	$Q_{gs}$			-	8	-			
Gate-drain charge	$Q_{gd}$			-	14	-			
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	15	30	ns		
Rise time	$t_r$			-	24	48			
Turn-off delay time	$t_{d(off)}$			-	34	68			
Fall time	$t_f$			-	18	36			
Gate input resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$		-	0.85	-	$\Omega$		
<b>Drain-Source Body Diode Characteristics</b>									
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	14.5	A		
Pulsed diode forward current	$I_{SM}$			-	-	28			
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 7.5\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V		
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 7.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	265	-	ns		
Reverse recovery charge	$Q_{rr}$			-	3.2	-	$\mu\text{C}$		
Reverse recovery current	$I_{RRM}$			-	23	-	A		

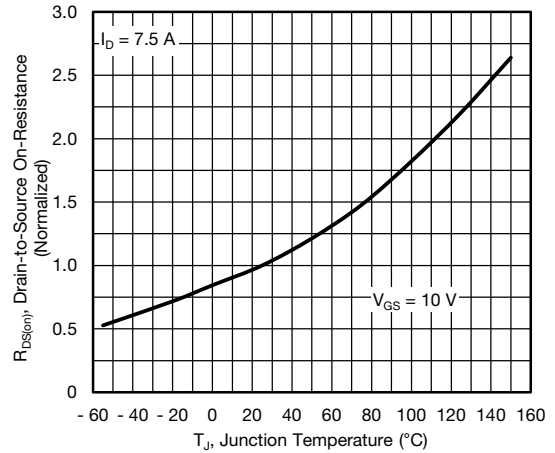
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

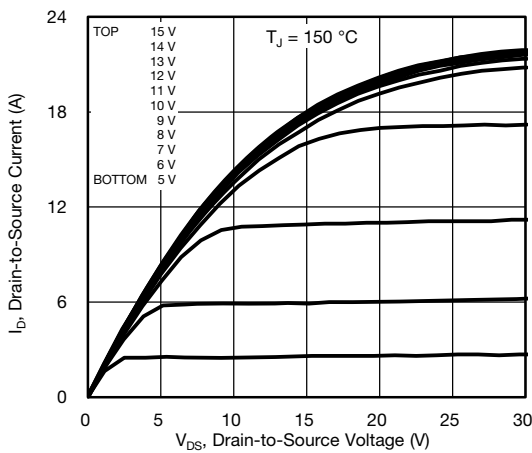
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



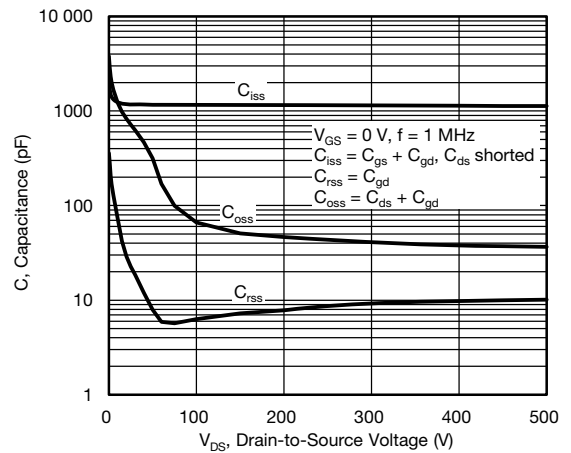
**Fig. 1 - Typical Output Characteristics**



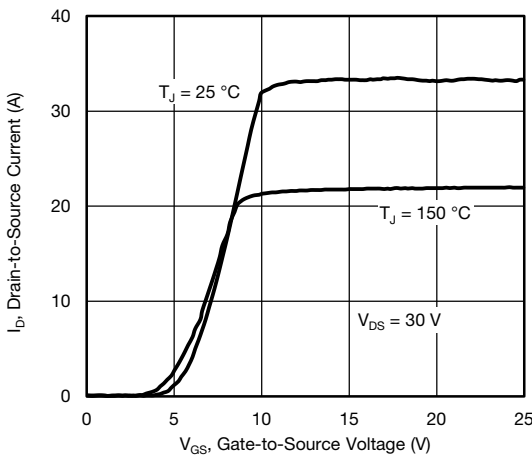
**Fig. 4 - Normalized On-Resistance vs. Temperature**



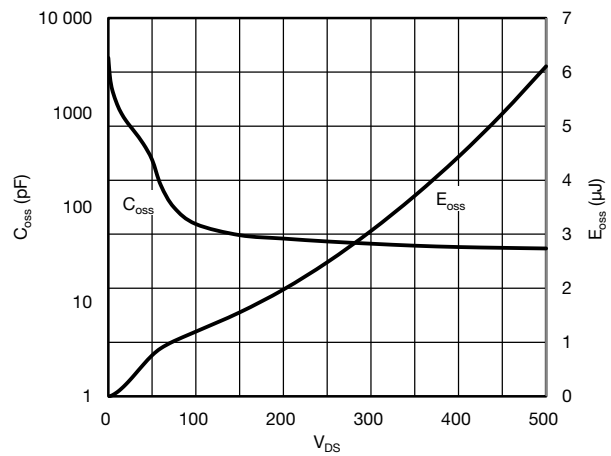
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - C<sub>oss</sub> and E<sub>oss</sub> vs. V<sub>DS</sub>**

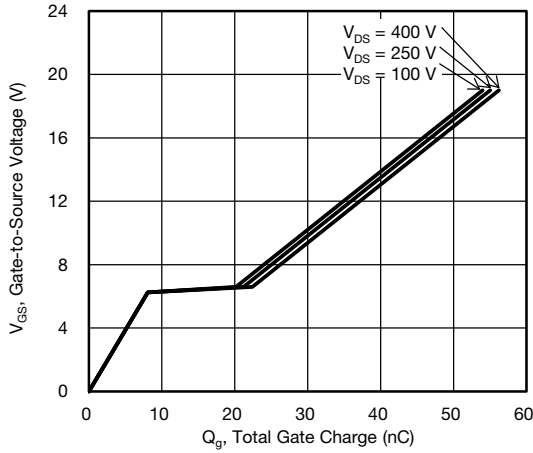


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

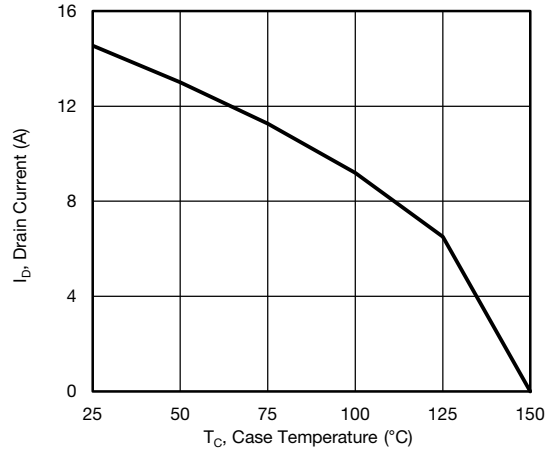


Fig. 10 - Maximum Drain Current vs. Case Temperature

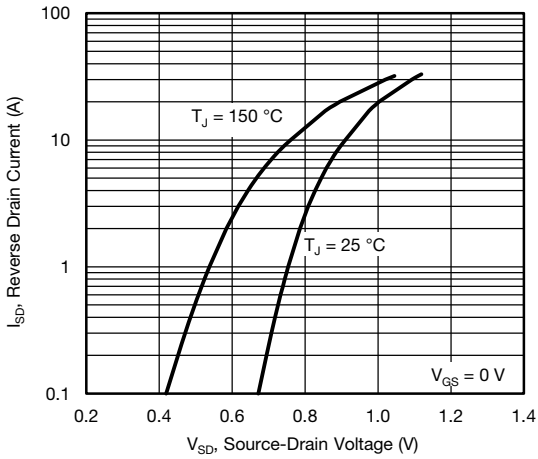


Fig. 8 - Typical Source-Drain Diode Forward Voltage

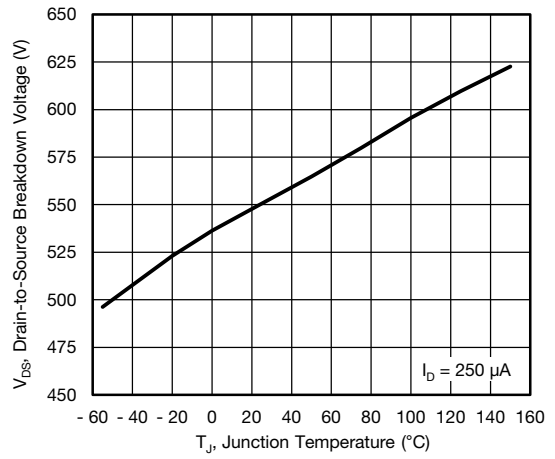


Fig. 11 - Temperature vs. Drain-to-Source Voltage

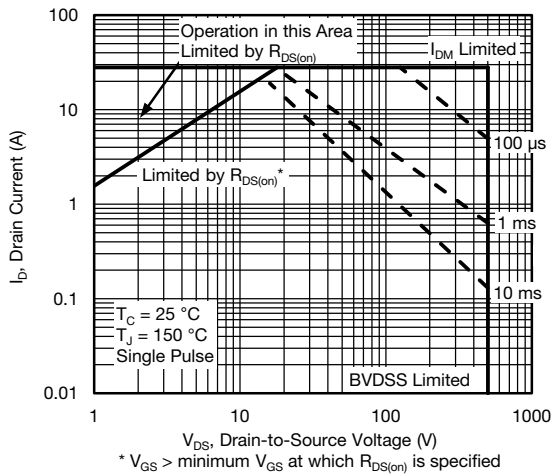
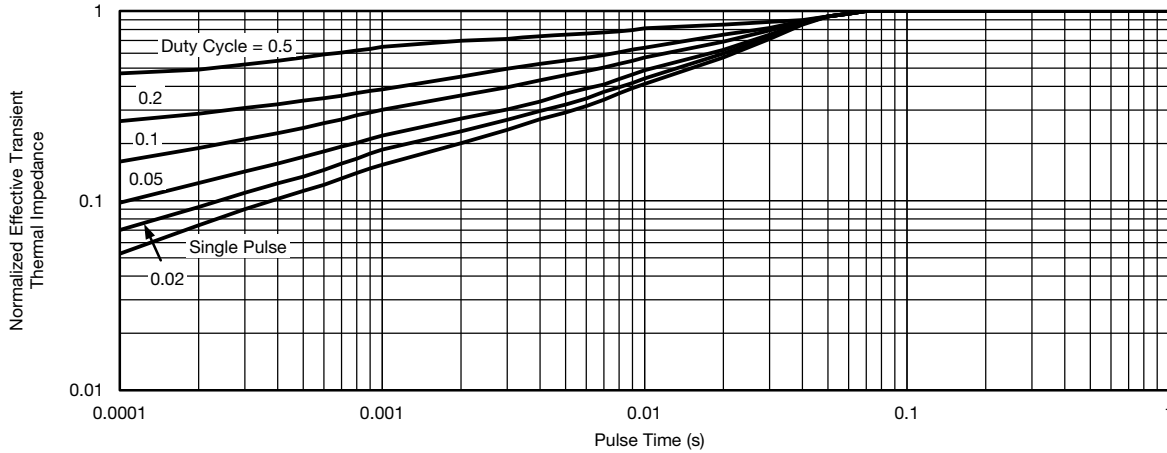


Fig. 9 - Maximum Safe Operating Area



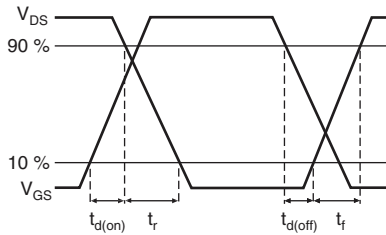
**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**



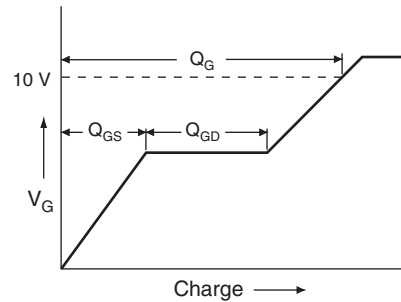
**Fig. 13 - Switching Time Test Circuit**



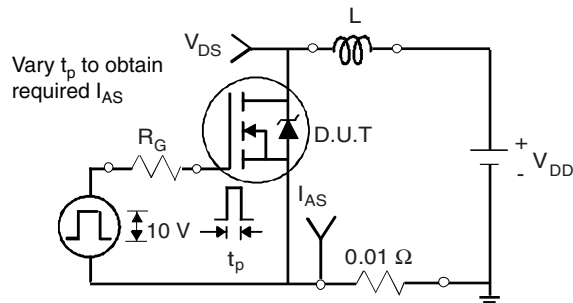
**Fig. 16 - Unclamped Inductive Waveforms**



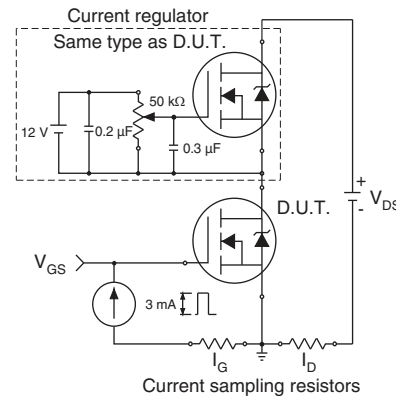
**Fig. 14 - Switching Time Waveforms**



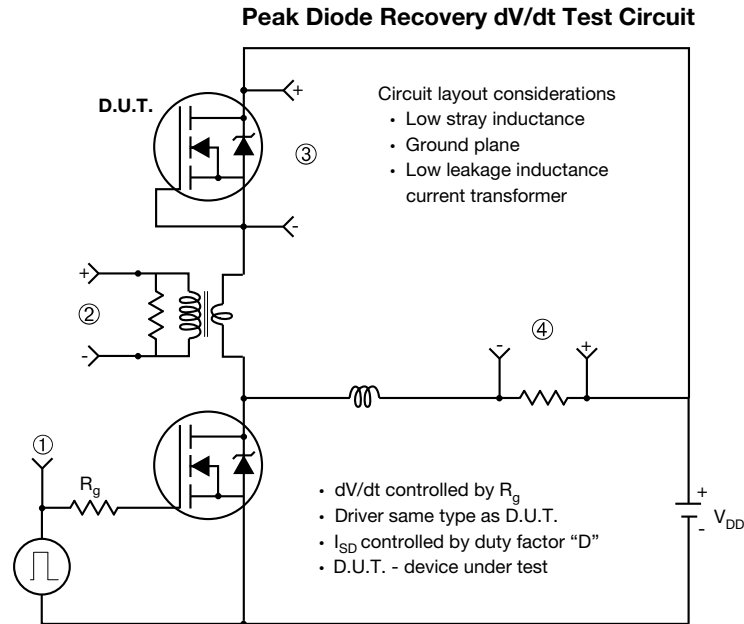
**Fig. 17 - Basic Gate Charge Waveform**



**Fig. 15 - Unclamped Inductive Test Circuit**



**Fig. 18 - Gate Charge Test Circuit**



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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